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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I <sup>2</sup> C, IrDA, SD, SPI, UART/USART
Peripherals	DMA, I <sup>2</sup> S, LVD, POR, PWM, WDT
Number of I/O	104
Program Memory Size	512KB (512K × 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 46x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LBGA
Supplier Device Package	144-MAPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dn512vmd10

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# 3.6 Relationship between ratings and operating requirements



# 3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

# 3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

## 3.8.1 Example 1

Symbol	Description	Min.	Тур.	Max.	Unit
I <sub>WP</sub>	Digital I/O weak pullup/pulldown	10	70	130	μΑ
	current				

This is an example of an operating behavior that includes a typical value:

## 3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



# 3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T <sub>A</sub>	Ambient temperature	25	٥°C
V <sub>DD</sub>	3.3 V supply voltage	3.3	V

K10 Sub-Family Data Sheet, Rev. 2, 12/2012.

3. Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions – TEM Cell and Wideband TEM Cell Method

## 5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- 1. Go to www.freescale.com.
- 2. Perform a keyword search for "EMC design."

## 5.2.8 Capacitance attributes

### Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C <sub>IN_A</sub>	Input capacitance: analog pins	—	7	pF
C <sub>IN_D</sub>	Input capacitance: digital pins	—	7	pF

# 5.3 Switching specifications

## 5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes	
Normal run mode						
f <sub>SYS</sub>	System and core clock	—	100	MHz		
f <sub>BUS</sub>	Bus clock	—	50	MHz		
FB_CLK	FlexBus clock	—	50	MHz		
f <sub>FLASH</sub>	Flash clock	—	25	MHz		
f <sub>LPTMR</sub>	LPTMR clock	—	25	MHz		
	VLPR mode <sup>1</sup>		•	•	•	
f <sub>SYS</sub>	System and core clock	—	4	MHz		
f <sub>BUS</sub>	Bus clock	—	4	MHz		
FB_CLK	FlexBus clock	—	4	MHz		
f <sub>FLASH</sub>	Flash clock	—	0.5	MHz		
f <sub>ERCLK</sub>	External reference clock	—	16	MHz		
f <sub>LPTMR_pin</sub>	LPTMR clock	—	25	MHz		
f <sub>LPTMR_ERCLK</sub>	LPTMR external reference clock		16	MHz		

Table continues on the next page...

- 1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
- 2. The greater synchronous and asynchronous timing must be met.
- 3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
- 4. 75pF load
- 5. 15pF load

# 5.4 Thermal specifications

## 5.4.1 Thermal operating requirements

### Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
TJ	Die junction temperature	-40	125	°C
T <sub>A</sub>	Ambient temperature	-40	105	°C

## 5.4.2 Thermal attributes

Board type	Symbol	Description	144 LQFP	144 MAPBGA	Unit	Notes
Single-layer (1s)	R <sub>θJA</sub>	Thermal resistance, junction to ambient (natural convection)	45	48	°C/W	1
Four-layer (2s2p)	R <sub>θJA</sub>	Thermal resistance, junction to ambient (natural convection)	36	29	°C/W	1
Single-layer (1s)	R <sub>eJMA</sub>	Thermal resistance, junction to ambient (200 ft./ min. air speed)	36	38	°C/W	1
Four-layer (2s2p)	R <sub>eJMA</sub>	Thermal resistance, junction to ambient (200 ft./ min. air speed)	30	25	°C/W	1

Table continues on the next page ...

Symbol	Description	Min.	Max.	Unit
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8	—	ns

## Table 13. JTAG limited voltage range electricals (continued)

### Table 14. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	20	
	Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1	_	ns
J3	TCLK clock pulse width			
	Boundary Scan	50	—	ns
	JTAG and CJTAG	25	_	ns
	Serial Wire Debug	12.5	_	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0		ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	_	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	TRST assert time	100		ns
J14	TRST setup time (negation) to TCLK high	8		ns



Figure 5. Test clock input timing





# 6.2 System modules

There are no specifications necessary for the device's system modules.

# 6.3 Clock modules

## 6.3.1 MCG specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f <sub>ints_ft</sub>	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	_	32.768	—	kHz	
f <sub>ints_t</sub>	Internal reference frequency (slow clock) — user trimmed	31.25	_	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	_	± 0.3	± 0.6	%f <sub>dco</sub>	1
$\Delta f_{dco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM only	_	± 0.2	± 0.5	%f <sub>dco</sub>	1
Δf <sub>dco_t</sub>	Total deviation of trimmed average DCO output frequency over voltage and temperature	_	+0.5/-0.7	± 3	%f <sub>dco</sub>	1
∆f <sub>dco_t</sub>	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C	_	± 0.3	± 3	%f <sub>dco</sub>	1
f <sub>intf_ft</sub>	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C	—	4	_	MHz	
f <sub>intf_t</sub>	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C	3	—	5	MHz	
f <sub>loc_low</sub>	Loss of external clock minimum frequency — RANGE = 00	(3/5) x f <sub>ints_t</sub>			kHz	
f <sub>loc_high</sub>	Loss of external clock minimum frequency — RANGE = 01, 10, or 11	(16/5) x f <sub>ints_t</sub>	—	_	kHz	

### Table 15. MCG specifications

Table continues on the next page...

K10 Sub-Family Data Sheet, Rev. 2, 12/2012.

## 6.3.2.2 Oscillator frequency specifications Table 17. Oscillator frequency specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f <sub>osc_lo</sub>	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	_	40	kHz	
f <sub>osc_hi_1</sub>	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	3	_	8	MHz	
f <sub>osc_hi_2</sub>	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	_	32	MHz	
f <sub>ec_extal</sub>	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t <sub>dc_extal</sub>	Input clock duty cycle (external clock mode)	40	50	60	%	
t <sub>cst</sub>	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	_	750	_	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)		250		ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	_	0.6	_	ms	•
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	_	1	_	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.

2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.

3. Proper PC board layout procedures must be followed to achieve specifications.

4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG\_S register being set.

## NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

## 6.3.3 32 kHz Oscillator Electrical Characteristics

This section describes the module electrical characteristics.

# 6.3.3.1 32 kHz oscillator DC electrical specifications

Table 18. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V <sub>BAT</sub>	Supply voltage	1.71	—	3.6	V
R <sub>F</sub>	Internal feedback resistor	—	100	_	MΩ

Table continues on the next page ...

### K10 Sub-Family Data Sheet, Rev. 2, 12/2012.

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	Byte-write to FlexRAM execution time:					
t <sub>eewr8b32k</sub>	32 KB EEPROM backup	—	385	1800	μs	
t <sub>eewr8b64k</sub>	64 KB EEPROM backup	—	475	2000	μs	
t <sub>eewr8b128k</sub>	128 KB EEPROM backup	—	650	2400	μs	
t <sub>eewr8b256k</sub>	• 256 KB EEPROM backup	—	1000	3200	μs	
	Word-write to FlexRAM	for EEPRON	A operation			
t <sub>eewr16bers</sub>	Word-write to erased FlexRAM location execution time	_	175	260	μs	
	Word-write to FlexRAM execution time:					
t <sub>eewr16b32k</sub>	32 KB EEPROM backup	—	385	1800	μs	
t <sub>eewr16b64k</sub>	64 KB EEPROM backup	—	475	2000	μs	
t <sub>eewr16b128k</sub>	128 KB EEPROM backup	—	650	2400	μs	
t <sub>eewr16b256k</sub>	• 256 KB EEPROM backup	—	1000	3200	μs	
	Longword-write to FlexRA	M for EEPR	OM operatior	ו	1	•
t <sub>eewr32bers</sub>	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
	Longword-write to FlexRAM execution time:					
t <sub>eewr32b32k</sub>	• 32 KB EEPROM backup	—	630	2050	μs	
t <sub>eewr32b64k</sub>	64 KB EEPROM backup	—	810	2250	μs	
t <sub>eewr32b128k</sub>	128 KB EEPROM backup	_	1200	2675	μs	
t <sub>eewr32b256k</sub>	• 256 KB EEPROM backup	—	1900	3500	μs	

Table 21. Flash command timing specifications (continued)

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

### 6.4.1.3 Flash high voltage current behaviors Table 22. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I <sub>DD_PGM</sub>	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I <sub>DD_ERS</sub>	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

Peripheral operating requirements and behaviors



Figure 9. EEPROM backup writes to FlexRAM

# 6.4.2 EzPort Switching Specifications

Table 24.	EzPort switching	specifications
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Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	f <sub>SYS</sub> /2	MHz
EP1a	EZP_CK frequency of operation (READ command)		f <sub>SYS</sub> /8	MHz
EP2	EZP_CS negation to next EZP_CS assertion	2 x t <sub>EZP_CK</sub>	—	ns
EP3	EZP_CS input valid to EZP_CK high (setup)	5		ns
EP4	EZP_CK high to EZP_CS input invalid (hold)	5		ns
EP5	EZP_D input valid to EZP_CK high (setup)	2		ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid		16	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0		ns
EP9	EZP_CS negation to EZP_Q tri-state	—	12	ns

2. Specification is valid for all FB\_AD[31:0] and FB\_TA.

### Table 26. Flexbus full voltage range switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	FB_CLK	MHz	
FB1	Clock period	1/FB_CLK	_	ns	
FB2	Address, data, and control output valid	—	13.5	ns	1
FB3	Address, data, and control output hold	0	_	ns	1
FB4	Data and FB_TA input setup	13.7	_	ns	2
FB5	Data and FB_TA input hold	0.5	_	ns	2

1. Specification is valid for all FB\_AD[31:0], FB\_BE/BWEn, FB\_CSn, FB\_OE, FB\_R/W, FB\_TBST, FB\_TSIZ[1:0], FB\_ALE, and FB\_TS.

2. Specification is valid for all FB\_AD[31:0] and  $\overline{FB_TA}$ .





Figure 12. FlexBus write timing diagram

# 6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

# 6.6 Analog

Symbol	Description	Conditions <sup>1</sup>	Min.	Typ. <sup>2</sup>	Max.	Unit	Notes
EIL	Input leakage error			$I_{In} \times R_{AS}$		mV	I <sub>In</sub> = leakage current
							(refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	—	1.715	—	mV/°C	
V <sub>TEMP25</sub>	Temp sensor voltage	25 °C		719	_	mV	

### Table 28. 16-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ , $V_{REFL} = V_{SSA}$ ) (continued)

- 1. All accuracy numbers assume the ADC is calibrated with  $V_{\mathsf{REFH}}$  =  $V_{\mathsf{DDA}}$
- Typical values assume V<sub>DDA</sub> = 3.0 V, Temp = 25°C, f<sub>ADCK</sub> = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
- 4. 1 LSB =  $(V_{REFH} V_{REFL})/2^N$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.









Typical ADC 16-bit Single-Ended ENOB vs ADC Clock 100Hz, 90% FS Sine Input



### 6.6.1.3 16-bit ADC with PGA operating conditions Table 29. 16-bit ADC with PGA operating conditions

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
V <sub>DDA</sub>	Supply voltage	Absolute	1.71	—	3.6	V	
V <sub>REFPGA</sub>	PGA ref voltage		VREF_OU T	VREF_OU T	VREF_OU T	V	2, 3
V <sub>ADIN</sub>	Input voltage		V <sub>SSA</sub>	—	V <sub>DDA</sub>	V	
V <sub>CM</sub>	Input Common Mode range		V <sub>SSA</sub>	_	V <sub>DDA</sub>	V	
R <sub>PGAD</sub>	Differential input	Gain = 1, 2, 4, 8	_	128	—	kΩ	IN+ to IN- <sup>4</sup>
	impedance	Gain = 16, 32	—	64	—		
		Gain = 64	_	32	—		
R <sub>AS</sub>	Analog source resistance		—	100	_	Ω	5
T <sub>S</sub>	ADC sampling time		1.25	_		μs	6

Table continues on the next page...

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
C <sub>rate</sub>	ADC conversion	≤ 13 bit modes	18.484	_	450	Ksps	7
	rate	No ADC hardware averaging					
	Continuous conversions enabled						
		Peripheral clock = 50 MHz					
		16 bit modes	37.037	_	250	Ksps	8
		No ADC hardware averaging					
		Continuous conversions enabled					
		Peripheral clock = 50 MHz					

### Table 29. 16-bit ADC with PGA operating conditions (continued)

- 1. Typical values assume V<sub>DDA</sub> = 3.0 V, Temp = 25°C, f<sub>ADCK</sub> = 6 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- 2. ADC must be configured to use the internal voltage reference (VREF\_OUT)
- 3. PGA reference is internally connected to the VREF\_OUT pin. If the user wishes to drive VREF\_OUT with a voltage other than the output of the VREF module, the VREF module must be disabled.
- 4. For single ended configurations the input impedance of the driven input is R<sub>PGAD</sub>/2
- 5. The analog source resistance (R<sub>AS</sub>), external to MCU, should be kept as minimum as possible. Increased R<sub>AS</sub> causes drop in PGA gain without affecting other performances. This is not dependent on ADC clock frequency.
- The minimum sampling time is dependent on input signal frequency and ADC mode of operation. A minimum of 1.25µs time should be allowed for F<sub>in</sub>=4 kHz at 16-bit differential mode. Recommended ADC setting is: ADLSMP=1, ADLSTS=2 at 8 MHz ADC clock.
- 7. ADC clock = 18 MHz, ADLSMP = 1, ADLST = 00, ADHSC = 1
- 8. ADC clock = 12 MHz, ADLSMP = 1, ADLST = 01, ADHSC = 1

### 6.6.1.4 16-bit ADC with PGA characteristics with Chop enabled (ADC\_PGA[PGACHPb] =0) Table 30. 16-bit ADC with PGA characteristics

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
I <sub>DDA_PGA</sub>	Supply current	Low power (ADC_PGA[PGALPb]=0)	_	420	644	μA	2
I <sub>DC_PGA</sub>	Input DC current		$\frac{2}{R_{\rm PGAD}} \left( \frac{\left( V_{\rm REFPGA} \times 0.583 \right) - V_{\rm CM}}{({\rm Gain}+1)} \right)$			A	3
		Gain =1, V <sub>REFPGA</sub> =1.2V, V <sub>CM</sub> =0.5V	_	1.54	_	μA	
		Gain =64, $V_{REFPGA}$ =1.2V, $V_{CM}$ =0.1V	_	0.57	—	μA	

Table continues on the next page ...

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
SFDR	Spurious free dynamic range	• Gain=1 • Gain=64	85 53	105 88	_	dB dB	16-bit differential mode,
							Average=32, f <sub>in</sub> =100Hz
ENOB	Effective number	Gain=1, Average=4	11.6	13.4		bits	16-bit
	of bits	• Gain=1, Average=8	8.0	13.6	—	bits	differential mode.fin=100Hz
		• Gain=64, Average=4	7.2	9.6	—	bits	
		• Gain=64, Average=8	6.3	9.6	—	bits	
		• Gain=1, Average=32	12.8	14.5	—	bits	
		• Gain=2, Average=32	11.0	14.3	—	bits	
		• Gain=4, Average=32	7.9	13.8	—	bits	
		• Gain=8, Average=32	7.3	13.1	—	bits	
		• Gain=16, Average=32	6.8	12.5	—	bits	
		• Gain=32, Average=32	6.8	11.5	—	bits	
		• Gain=64, Average=32	7.5	10.6	—	bits	
SINAD	Signal-to-noise plus distortion ratio	See ENOB	6.02	× ENOB +	1.76	dB	

### Table 30. 16-bit ADC with PGA characteristics (continued)

- 1. Typical values assume  $V_{DDA}$  =3.0V, Temp=25°C,  $f_{ADCK}$ =6MHz unless otherwise stated.
- 2. This current is a PGA module adder, in addition to ADC conversion currents.
- Between IN+ and IN-. The PGA draws a DC current from the input terminals. The magnitude of the DC current is a strong function of input common mode voltage (V<sub>CM</sub>) and the PGA gain.
- 4. Gain =  $2^{PGAG}$
- 5. After changing the PGA gain setting, a minimum of 2 ADC+PGA conversions should be ignored.
- 6. Limit the input signal swing so that the PGA does not saturate during operation. Input signal swing is dependent on the PGA reference voltage and gain setting.

## 6.6.2 CMP and 6-bit DAC electrical specifications Table 31. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Supply voltage	1.71	—	3.6	V
I <sub>DDHS</sub>	Supply current, High-speed mode (EN=1, PMODE=1)	_	—	200	μA
I <sub>DDLS</sub>	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V <sub>AIN</sub>	Analog input voltage	$V_{SS} - 0.3$	_	V <sub>DD</sub>	V
V <sub>AIO</sub>	Analog input offset voltage	_	—	20	mV

Table continues on the next page...

Symbol	Description	Min.	Тур.	Max.	Unit
V <sub>H</sub>	Analog comparator hysteresis <sup>1</sup>				
	• CR0[HYSTCTR] = 00	_	5	—	mV
	• CR0[HYSTCTR] = 01	_	10		mV
	• CR0[HYSTCTR] = 10	_	20	_	mV
	<ul> <li>CR0[HYSTCTR] = 11</li> </ul>	_	30	_	mV
V <sub>CMPOh</sub>	Output high	V <sub>DD</sub> – 0.5			V
V <sub>CMPOI</sub>	Output low	—	_	0.5	V
t <sub>DHS</sub>	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t <sub>DLS</sub>	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay <sup>2</sup>	—	_	40	μs
I <sub>DAC6b</sub>	6-bit DAC current adder (enabled)	—	7	_	μA
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB <sup>3</sup>
DNL	6-bit DAC differential non-linearity	-0.3	—	0.3	LSB

## Table 31. Comparator and 6-bit DAC electrical specifications (continued)

1. Typical hysteresis is measured with input voltage range limited to 0.6 to  $V_{DD}$ -0.6V.

2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

3. 1 LSB =  $V_{reference}/64$ 





Figure 19. Offset at half scale vs. temperature

## 6.6.4 Voltage reference electrical specifications

Table 34.	VREF full-range	operating	requirements
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Symbol	Description	Min.	Max.	Unit	Notes
V <sub>DDA</sub>	Supply voltage	1.71	3.6	V	
T <sub>A</sub>	Temperature	Operating temperature range of the device		°C	
CL	Output load capacitance	1(	00	nF	1, 2

1. C<sub>L</sub> must be connected to VREF\_OUT if the VREF\_OUT functionality is being used for either an internal or external reference.

 The load capacitance should not exceed +/-25% of the nominal specified C<sub>L</sub> value over the operating temperature range of the device.



Figure 31. K10 144 LQFP Pinout Diagram

#### **Revision History**

	1	2	3	4	5	6	7	8	9	10	11	12	
A	PTD7	PTD6/ LLWU_P15	PTD5	PTD4/ LLWU_P14	PTD0/ LLWU_P12	PTC16	PTC12	PTC8	PTC4/ LLWU_P8	NC	PTC3/ LLWU_P7	PTC2	A
в	PTD12	PTD11	PTD10	PTD3	PTC19	PTC15	PTC11/ LLWU_P11	PTC7	PTD9	NC	PTC1/ LLWU_P6	PTC0	в
с	PTD15	PTD14	PTD13	PTD2/ LLWU_P13	PTC18	PTC14	PTC10	PTC6/ LLWU_P10	PTD8	NC	PTB23	PTB22	с
D	PTE2/ LLWU_P1	PTE1/ LLWU_P0	PTE0	PTD1	PTC17	PTC13	PTC9	PTC5/ LLWU_P9	PTB21	PTB20	PTB19	PTB18	D
E	PTE6	PTE5	PTE4/ LLWU_P2	PTE3	VDD	VDD	VDD	VDD	PTB17	PTB16	PTB11	PTB10	E
F	PTE10	PTE9	PTE8	PTE7	VDD	VSS	VSS	VDD	PTB9	PTB8	PTB7	PTB6	F
G	PTE18	PTE19	PTE12	PTE11	VREFH	VREFL	VSS	VSS	PTB5	PTB4	PTB3	PTB2	G
н	PTE16	PTE17	VSS	PTE28	VDDA	VSSA	VSS	VSS	PTB1	PTB0/ LLWU_P5	PTA29	PTA28	н
J	ADC0_DP1	ADC0_DM1	ADC0_SE16/ CMP1_IN2/ ADC0_SE21	PTE27	PTA0	PTA1	PTA6	PTA7	PTA13/ LLWU_P4	PTA27	PTA26	PTA25	J
к	ADC1_DP1	ADC1_DM1	ADC1_SE16/ CMP2_IN2/ ADC0_SE22	PTE26	PTE25	PTA2	PTA3	PTA8	PTA12	PTA16	PTA17	PTA24	к
L	PGA0_DP/ ADC0_DP0/ ADC1_DP3	PGA0_DM/ ADC0_DM0/ ADC1_DM3	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC1_OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_SE23	RTC _WAKEUP_B	VBAT	PTA4/ LLWU_P3	PTA9	PTA11	PTA14	PTA15	RESET_b	L
м	PGA1_DP/ ADC1_DP0/ ADC0_DP3	PGA1_DM/ ADC1_DM0/ ADC0_DM3	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	PTE24	NC	EXTAL32	XTAL32	PTA5	PTA10	VSS	PTA19	PTA18	м
ļ	1	2	3	4	5	6	7	8	9	10	11	12	1

Figure 32. K10 144 MAPBGA Pinout Diagram

#### **Revision History** 9

12/2012

The following table provides a revision history for this document.

Replaced TBDs throughout.

		······································
Rev. No.	Date	Substantial Changes
1	6/2012	Initial public revision

### Table 50. Revision History

1 2

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